

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (π -MOSVI)

2SK3089

HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS

CHOPPER REGULATOR, DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

INDUSTRIAL APPLICATIONS

Unit in mm

- Low Drain-Source ON Resistance : $R_{DS(ON)} = 25 \text{ m}\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 20 \text{ S}$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100 \mu\text{A}$ (Max.) ($V_{DS} = 30 \text{ V}$)
- Enhancement-Mode : $V_{th} = 1.5 \sim 3.0 \text{ V}$ ($V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$)

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	30	V
Drain-Gate Voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	30	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	DC	I_D	40	A
	Pulse	I_{DP}	80	
Drain Power Dissipation ($T_c = 25^\circ\text{C}$)		P_D	50	W
Single Pulse Avalanche Energy**		E_{AS}	134	mJ
Avalanche Current		I_{AR}	40	A
Repetitive Avalanche Energy*		E_{AR}	5	mJ
Channel Temperature		T_{ch}	150	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	$-55 \sim 150$	$^\circ\text{C}$

THERMAL CHARACTERISTICS

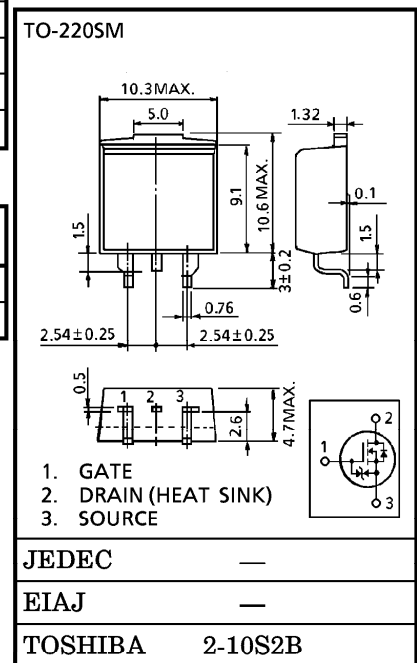
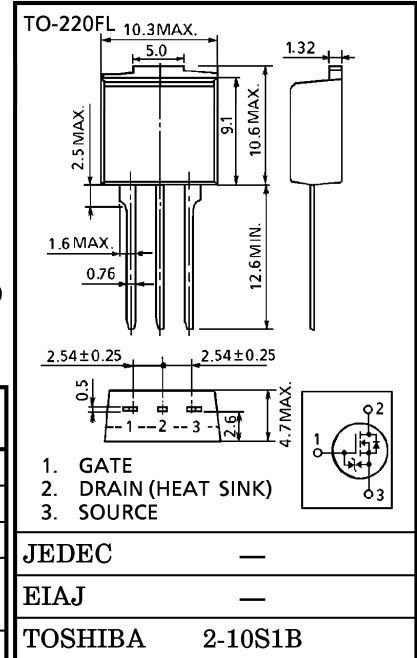
CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	2.5	$^\circ\text{C/W}$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	83.3	$^\circ\text{C/W}$

Note ;

* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

** $V_{DD} = 25 \text{ V}$, Starting $T_{ch} = 25^\circ\text{C}$, $L = 60 \mu\text{H}$, $R_G = 25 \Omega$, $I_{AR} = 40 \text{ A}$

This transistor is an electrostatic sensitive device. Please handle with caution.



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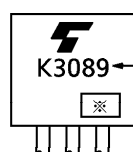
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$	—	—	± 10	μA
Drain Cut-off Current		I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$	—	—	100	μA
Drain-Source Breakdown Voltage		$V(\text{BR})_{DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	30	—	—	V
Gate Threshold Voltage		V_{th}	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	1.5	—	3.0	V
Drain-Source ON Resistance		$R_{DS(\text{ON})}$	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$	—	25	30	$\text{m}\Omega$
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 20\text{ A}$	10	20	—	S
Input Capacitance		C_{iss}	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	920	—	pF
Reverse Transfer Capacitance		C_{rss}		—	290	—	
Output Capacitance		C_{oss}		—	420	—	
Switching Time	Rise Time	t_r	<p>$V_{GS} = 10\text{ V}, 0\text{ V}$ $I_D = 20\text{ A}$ $R_L = 1.2\ \Omega$ $V_{DD} \doteq 24\text{ V}$</p>	—	10	—	ns
	Turn-on Time	t_{on}		—	17	—	
	Fall Time	t_f		—	40	—	
	Turn-off Time	t_{off}		$V_{IN} : t_r, t_f < 5\text{ ns}$ $\text{Duty} \leq 1\%, t_w = 10\ \mu\text{s}$	—	80	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q_g	$V_{DD} \doteq 24\text{ V}, V_{GS} = 10\text{ V}$ $I_D = 40\text{ A}$	—	23	—	nC
Gate-Source Charge		Q_{gs}		—	15	—	
Gate-Drain ("Miller") Charge		Q_{gd}		—	8	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	40	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	80	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = 40\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.7	V
Reverse Recovery Time	t_{rr}	$I_{DR} = 40\text{ A}, V_{GS} = 0\text{ V}$	—	80	—	ns
Reverse Recovery Charge	Q_{rr}	$dI_{DR}/dt = 50\text{ A}/\mu\text{s}$	—	130	—	nC

MARKING



※ Lot Number

□ □ — Month (Starting from Alphabet A)

— Year (Last Number of the Christian Era)